Unit: mm



TOSHIBA Field Effect Transistor Silicon P Channel MOS Type(U-MOSVI)

SSM6J502NU

Power Management Switch Applications

1.5V drive

Low ON-resistance: RDS(ON) = $60.5 \text{ m}\Omega \text{ (max) (@VGS} = -1.5 \text{ V)}$

RDS(ON) = 38.4 m Ω (max) (@V_{GS} = -1.8 V)

RDS(ON) = 28.3 m Ω (max) (@VGS = -2.5 V)

 $RDS(ON) = 23.1 \text{ m}\Omega \text{ (max) (@V}_{GS} = -4.5 \text{ V)}$

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unit | |
|----------------------|-------|-------------------------|------------|------|--|
| Drain-Source voltage | | VDSS | -20 | V | |
| Gate-Source voltage | | Vgss | ±8 | V | |
| Drain current | DC | ΙD | -6 | А | |
| | Pulse | IDP (Note 1) | -24 | | |
| Dawar diadiration | | P _D (Note 2) | 1 | 10/ | |
| Power dissipation | | t ≤ 10s | 2 W | | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature | | T _{stg} | −55 to 150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

> Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling

Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate,

Note 1: Ensure that the channel temperature does not exceed 150°C

Note 2: Mounted on FR4 board. $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ mm}, \text{Cu Pad: } 645 \text{ mm}^2)$

2.0 ±0.1 A В 2.0±0.1 Ф0.05 (M) A В 0.95 ±0.075 BOTTOM VIEW 1.2.5.6: Drain 3: Gate 4: Source UDFN6B **JEDEC JEITA TOSHIBA** 2-2AA1A

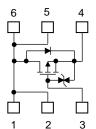
Weight: 8.5 mg (typ.)

Marking(Top View)

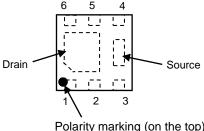
Polarity marking

@ 2019

Equivalent Circuit(Top View)



Pin Condition(Top View)



Polarity marking (on the top) *Electrodes: on the bottom

Start of commercial production 2010-11

2019-06-27



Electrical Characteristics (Ta = 25°C)

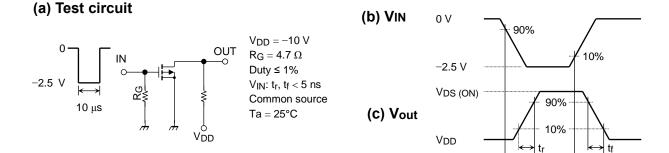
| Char | acteristic | Symbol | Test Conditions | | Min | Тур. | Max | Unit | | |
|--------------------------------|---------------|------------------|--|----------|------|------|------|-------|--|--|
| Davis Osama karakalana anti | -1-1 | V (BR) DSS | I _D = -1 mA, V _G S = 0 V | | -20 | _ | _ | V | | |
| Drain-Source breakdown voltage | | V (BR) DSX | I _D = -1 mA, V _G S = 5 V | (Note 4) | -15 | _ | _ |] ' [| | |
| Drain cut-off current | | I _{DSS} | V _{DS} = -20 V, V _{GS} = 0 V | | _ | _ | -1 | μА | | |
| Gate leakage current | | IGSS | $VGS = \pm 8 \text{ V}, VDS = 0 \text{ V}$ | | - | _ | ±1 | μΑ | | |
| Gate threshold voltage | | V _{th} | $V_{DS} = -3 V$, $I_{D} = -1 mA$ | | -0.3 | _ | -1.0 | V | | |
| Forward transfer admittance | | Yfs | V _{DS} = -3 V, I _D = -2.0 A | (Note 3) | 8.8 | 17.5 | _ | S | | |
| Drain-source ON-resistance | | RDS (ON) | I _D = -4.0 A, V _{GS} = -4.5 V | (Note 3) | - | 18.2 | 23.1 | mΩ | | |
| | | | I _D = -4.0 A, V _{GS} = -2.5 V | (Note 3) | - | 21.5 | 28.3 | | | |
| | | | I _D = -2.5 A, V _G S = -1.8 V | (Note 3) | | 26.1 | 38.4 | | | |
| | | | I _D = -1.5 A, V _G S = -1.5 V | (Note 3) | | 29.7 | 60.5 | | | |
| Input capacitance | | C _{iss} | | | | 1800 | _ | | | |
| Output capacitance | | Coss | V _{DS} = -10 V, V _{GS} = 0 V, f = 1 | _ | 205 | _ | pF | | | |
| Reverse transfer capacitance | | C _{rss} | | | | 190 | | _ | | |
| Total Gate Charge | | Qg | | | | 24.8 | _ | | | |
| Gate-Source Charge | | Q _{gs1} | V _{DD} = -10 V, I _D = -4.4 A V _{GS} = -4.5 V | | | 0.8 | _ | nC | | |
| Gate-Drain Charge | | Q _{gd} | | | _ | 6.8 | _ | | | |
| Switching time | Turn-on time | ton | V _{DD} = -10 V, I _D = -1.5 A, | | _ | 25 | _ | | | |
| | Turn-off time | t _{off} | $V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_{G} = 4.7 \Omega$ | | _ | 133 | _ | ns | | |
| Drain-Source forward voltage | | VDSF | I _D = 4 A, V _{GS} = 0 V | (Note 3) | _ | 0.7 | 1.2 | V | | |

Note 3: Pulse measurement.

Note 4: If a forward bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode.

Note that the drain-source breakdown voltage is lowered in this mode.

Switching Time Test Circuit



Precaution

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (-1 mA for the SSM6J502NU). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(onf)} < V_{th} < V_{GS(onf)}$.

 t_{on}

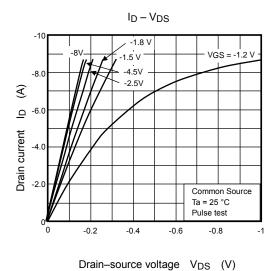
Take this into consideration when using the device.

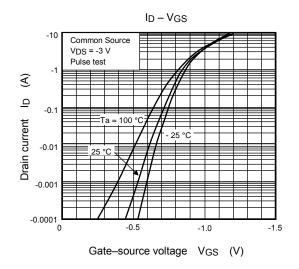
Handling Precaution

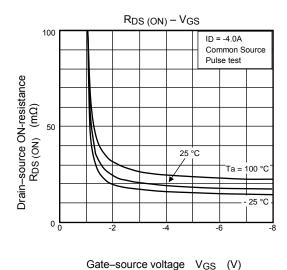
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

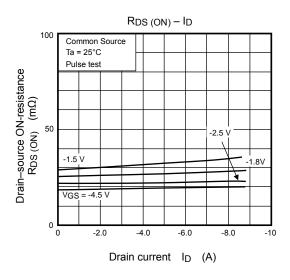
Thermal resistance Rth (ch-a) and power dissipation PD vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration

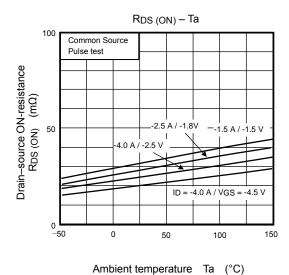


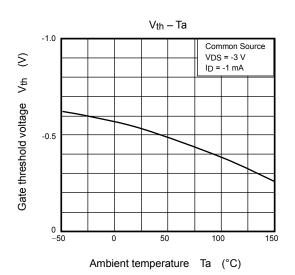




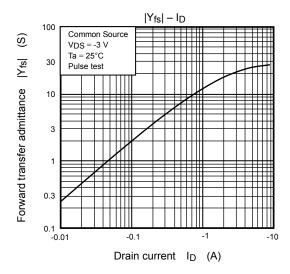


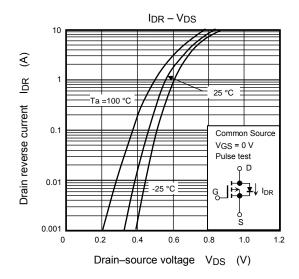


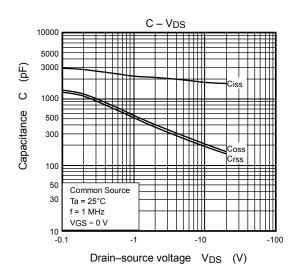


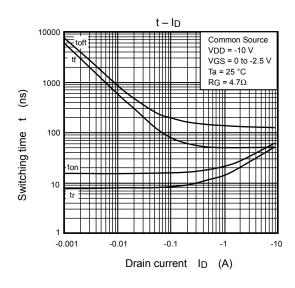


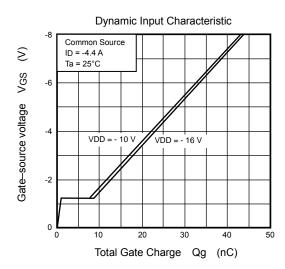




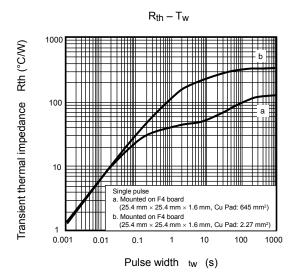


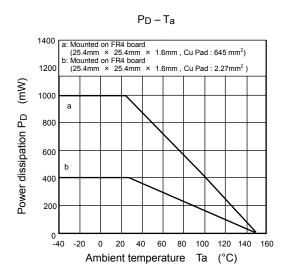












Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



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